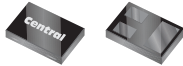


CTLDM7590
SURFACE MOUNT
P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET



Top View Bottom View

TLM3D6D8 CASE



www.centra-semi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CTLDM7590 is an enhancement-mode P-channel MOSFET designed for applications including high speed pulsed amplifiers and drivers. This MOSFET has beneficially low $r_{DS(ON)}$, low threshold voltage, and very low gate charge characteristics.

MARKING CODE: 2

FEATURES:

- ESD protection up to 2kV
- Power dissipation: 125mW
- Low $r_{DS(ON)}$
- Low threshold voltage
- Ultra small, ultra low profile 0.6mm x 0.8mm x 0.4mm TLM™ leadless surface mount package

APPLICATIONS:

- Load/Power Switches
- Boost/Buck Converters
- Battery Charging/Power Management

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Drain-Source Voltage
Gate-Source Voltage
Continuous Drain Current (Steady State)
Pulsed Drain Current, $t_p=10\mu\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{DS}	20	V
V_{GS}	8.0	V
I_D	140	mA
I_D	600	mA
P_D	125	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	1000	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

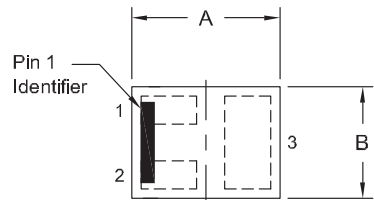
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=5.0\text{V}, V_{DS}=0$			100	nA
I_{DSS}	$V_{DS}=5.0\text{V}, V_{GS}=0$			50	nA
I_{DSS}	$V_{DS}=16\text{V}, V_{GS}=0$			100	nA
BV_{DSS}	$V_{GS}=0, I_D=250\mu\text{A}$	20			V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.4		1.0	V
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=100\text{mA}$		4.0	5.0	Ω
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=50\text{mA}$		5.5	7.0	Ω
$r_{DS(ON)}$	$V_{GS}=1.8\text{V}, I_D=20\text{mA}$		8.0	10	Ω
$r_{DS(ON)}$	$V_{GS}=1.5\text{V}, I_D=10\text{mA}$		11	17	Ω
$r_{DS(ON)}$	$V_{GS}=1.2\text{V}, I_D=1.0\text{mA}$		20		Ω
$Q_g(\text{tot})$	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$		0.50		nC
Q_{gs}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$		0.17		nC
Q_{gd}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=100\text{mA}$		0.11		nC
g_{FS}	$V_{DS}=5.0\text{V}, I_D=125\text{mA}$		140		mS
C_{rss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		4.0		pF
C_{iss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		10		pF
C_{oss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		3.7		pF
t_{on}	$V_{DD}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}$		35		ns
t_{off}	$V_{DD}=10\text{V}, V_{GS}=4.5\text{V}, I_D=200\text{mA}$		100		ns

R3 (21-September 2012)

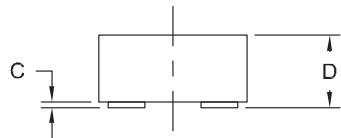
CTLDM7590
SURFACE MOUNT
P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET



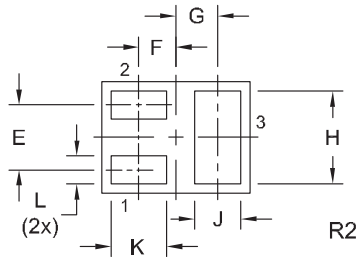
TLM3D6D8 CASE - MECHANICAL OUTLINE



TOP VIEW



SIDE VIEW

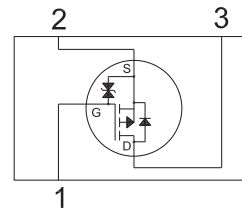


BOTTOM VIEW

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.029	0.034	0.75	0.85
B	0.021	0.026	0.55	0.65
C	0.000	0.002	0.00	0.05
D	0.012	0.016	0.31	0.40
E	0.014		0.35	
F	0.008		0.20	
G	0.009		0.225	
H	0.017	0.022	0.45	0.55
J	0.008	0.012	0.20	0.30
K	0.010	0.014	0.25	0.35
L	0.004	0.008	0.10	0.20

TLM3D6D8 (REV: R2)

PIN CONFIGURATION
(Bottom View)



LEAD CODE:

- 1) Gate
- 2) Source
- 3) Drain

MARKING CODE: 2

R3 (21-September 2012)

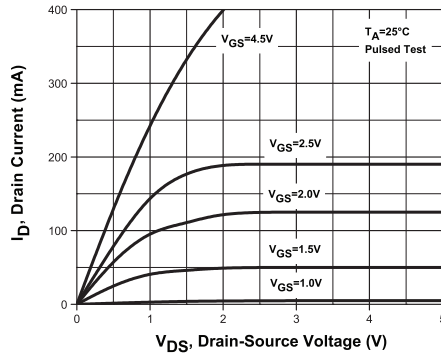
CTLDM7590



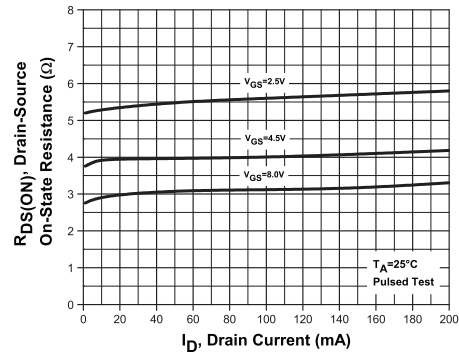
**SURFACE MOUNT
P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET**

TYPICAL ELECTRICAL CHARACTERISTICS

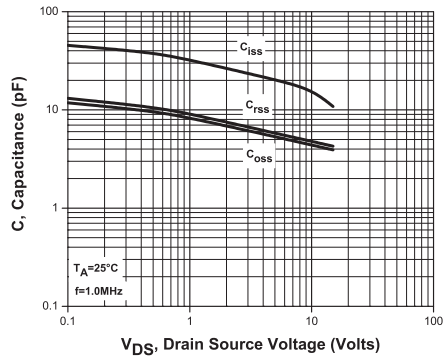
Output Characteristics



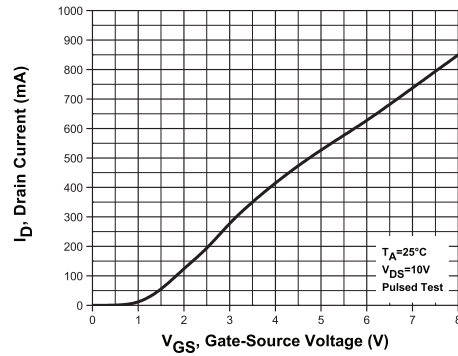
Drain Source On Resistance



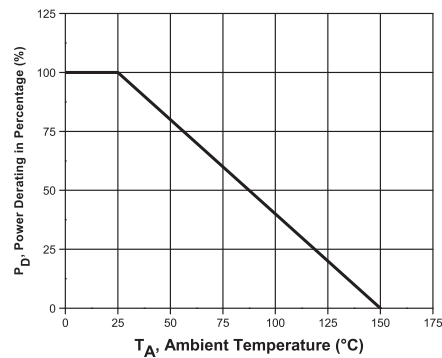
Capacitance



Transfer Characteristics



Normalized Power Derating



R3 (21-September 2012)